



1N4448

Small-Signal Diode - Fast Switching Rectifier
Reverse Voltage 100V Forward Current 150mA

Features

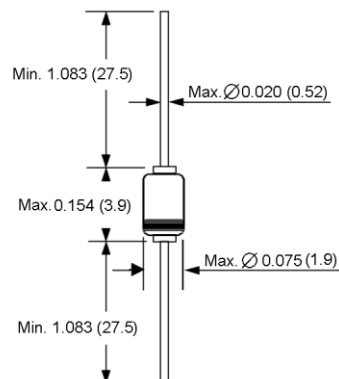
- ◆ Silicon Epitaxial Planar Diode
- ◆ Fast switching diode
- ◆ This diode is also available in other case styles including the MiniMELF case with the type designation LL4448.



DO-204AH (DO-35 Glass)

Mechanical Data

- ◆ Case: DO-35 Glass Case
- ◆ Weight: approx. 0.13g



Dimensions in inches and (millimeters)

Maximum Ratings and Thermal Characteristics

($T_A = 25^\circ\text{C}$ unless otherwise noted.)

Parameter	Symbol	Limit	Unit
Reverse voltage	V_R	75	Volts
Peak reverse voltage	V_{RM}	100	Volts
Average rectified current half wave rectification with resistive load at $T_{amb} = 25^\circ\text{C}$ and $f \geq 50\text{Hz}$ ⁽¹⁾	$I_{F(AV)}$	150	mA
Surge forward current at $t < 1\text{s}$ and $T_j = 25^\circ\text{C}$	I_{FSM}	500	mA
Power dissipation at $T_{amb} = 25^\circ\text{C}$ ⁽¹⁾	P_{tot}	500	mW
Thermal resistance junction to ambient air ⁽¹⁾	$R_{\theta JA}$	350	$^\circ\text{C/W}$
Junction temperature	T_j	175	$^\circ\text{C}$
Storage temperature range	T_s	-65 to +175	$^\circ\text{C}$

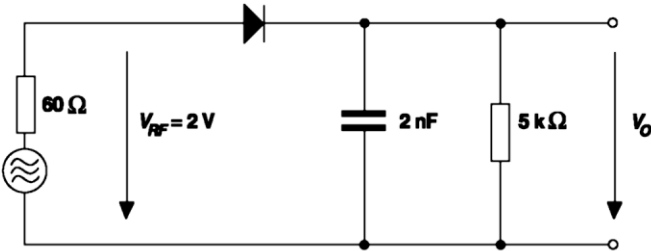
Notes: 1. Valid provided that leads at a distance of 8mm from case are kept at ambient temperature

Electrical Characteristics

(T_j=25°C unless otherwise noted.)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Forward voltage	V _F	I _F =5mA I _F =10mA	0.62 -	- -	0.72 1.0	Volt
Leakage current	I _R	V _R =20V V _R =75V V _R =20V, T _j =150°C	- - -	- - -	25 5.0 50	nA uA uA
Reverse breakdown voltage	V _{(BR)R}	I _R =100uA (pulsed)	100	-	-	Volts
Capacitance	C _{tot}	V _F =V _R =0V	-	-	4.0	pF
Reverse recovery time	t _{rr}	I _F =10mA, I _R =1mA V _R =6V, R _L =100Ω	-	-	4.0	ns
Rectification efficiency	η _V	f=100MHz, V _{RF} =2V	0.45	-	-	-

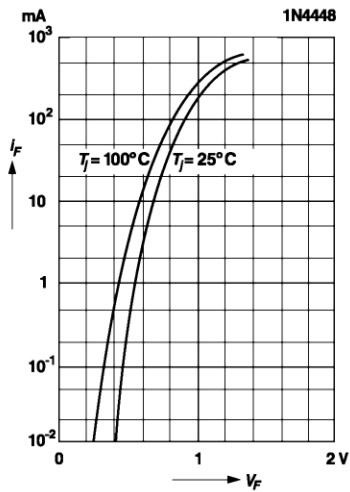
Rectification Efficiency Measurement Circuit



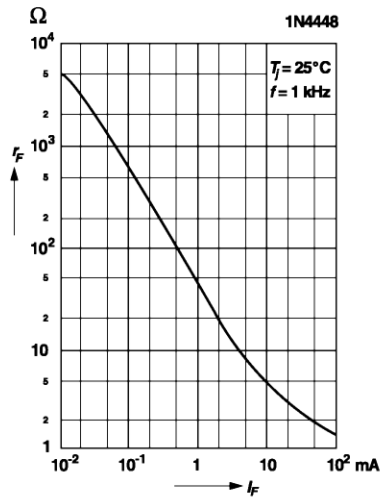
RATINGS AND CHARACTERISTIC CURVES

($T_A = 25^{\circ}\text{C}$ unless otherwise noted)

Forward characteristics

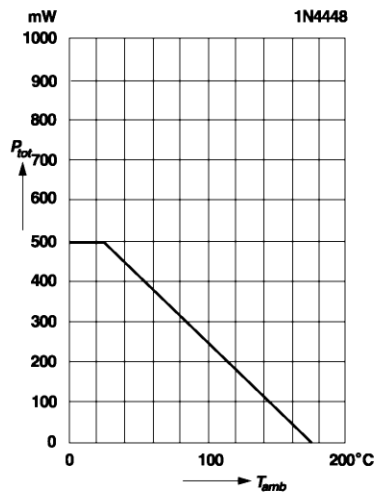


Dynamic forward resistance versus forward current

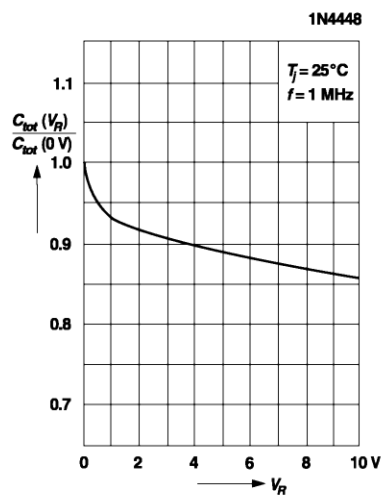


Admissible power dissipation versus ambient temperature

For conditions, see footnote in table "Absolute Maximum Ratings"



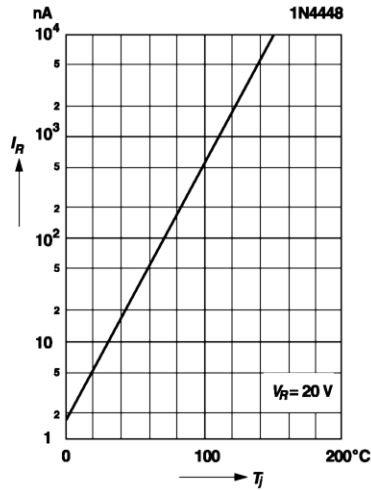
Relative capacitance versus reverse voltage



RATINGS AND CHARACTERISTIC CURVES

($T_A = 25^\circ\text{C}$ unless otherwise noted)

**Leakage current
versus junction temperature**



Admissible repetitive peak forward current versus pulse duration

For conditions, see footnote in table "Absolute Maximum Ratings"

